

HM9910

UNIVERSAL HIGH BRIGHTNESS LED DRIVER

FEATURES

- Efficiency
- Input voltage range
- Withstanding input voltage surge
- Output current range
- String of LEDs
- Constant-current LED driver
- Linear and PWM dimming capability

APPLICATIONS

- DC/DC or AC/DC LED driver
- RGB backlighting LED driver
- Backlighting of flat panel displays
- General-purpose constant current source
- Signage and decorative LED lighting
- Automotive
- Chargers

DESCRIPTION

The HM9910 is a PWM high-efficiency LED driver control IC. It allows efficient operation of highbrightness (HB) LEDs from 10VDC up to 600VDC voltage sources. The circuit controls an external MOSFET at fixed switching frequencies up to 300 kHz. The frequency can be programmed by using a single resistor. The device peculiarity is that a LED string is driven at a constant current rather than at a constant voltage, thus providing a constant light output and an enhanced reliability. The output current can be programmed between a few milliamps and up to more than 1.0A. A rugged high-voltage junction isolated process was used and enabled the device to withstand an input voltage surge up to 600V. The output current to a LED string is programmable to any value between zero and its maximum value by applying an external control voltage to the linear dimming control input. To allow the device to accept an external control signal with a duty ratio of 0 to 100% and a frequency of up to a few kilohertz the circuit has a low-frequency PWM dimming input.

>90%

10V to 600V

a few mA to more than 1A

1 pc to several hundreds

up to 600V

TYPICAL APPLICATION CIRCUIT





8-pin SO-8/DIP



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ABSOLUTE MAXIMUM RATINGS

V_{IN} to GND CS, LD, PWM_D, GATE to GND Continuous power dissipation (T_A = +25°C) (Note 1) 8-pin DIP (derate 9 mW/°C above +25°C) 8-pin SO-8 (derate 6.3 mW/°C above +25°C) Operating temperature range Junction temperature Storage temperature range -0.5V to +600V -0.3V to V_{DD}+0.3V

900mW 630mW -40°C to +85°C +125°C -65°C to +150°C

Stresses beyond those listed under **ABSOLUTE MAXIMUM RATINGS** may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

SYMBOL	unless noted otherwise) DESCRIPTION	MIN	TYP	MAX	UNITS	CONDITIONS
V _{INDC} ¹	Input DC supply voltage range	10.0		600	V	DC input voltage
	Shut-down mode supply current	0.5		1	mA	Pin PWM_D to GND, $V_{IN} = 8V$
V _{DD}	Internally regulated voltage	7.0	7.5	8.0	V	$V_{IN} = 10V$ to 600V, $I_{DD(ext)} = 0$, pin GATE is open
$\Delta V_{DD, load}$	V _{DD} load regulation	0	-	100	mV	$I_{DD(ext)} = 0$ to 1.0mA, 500pF at GATE; $R_{OSC} = 226$ kOhm, PWM_D = V _{DD}
V _{DD,max}	Maximal pin V _{DD} voltage			10.0	V	When an external voltage is applied to pin V _{DD}
I _{DD(ext)}	V _{DD} current available for external circuitry			0.7	mA	V _{IN} = 10V to 100V
UVLO	V _{DD} undervoltage lockout threshold	0.87* V _{DD}	0.89* V _{DD}	0.91* V _{DD}	%	Rising V_{IN}
Δυνιο	V _{DD} undervoltage lockout hysteresis		500		mV	Falling V _{IN}
V _{EN(lo)}	Pin PWM_D input low voltage			0.8	V	$V_{IN} = 10V$ to 600V
V _{EN(hi)}	Pin PWM_D input high voltage	2.0			V	$V_{IN} = 10V$ to 600V
R _{EN}	Pin PWM_D pull-down resistance	50	100	150	kOhm	$V_{\rm EN} = 5V$
dV _{CS}	Accuracy of Current Sense threshold voltage at wafer testing	-2.4%	0	2.4%	%	
V _{CS(hi)}	Current sense pull-in threshold voltage	238	250	262	mV	T _A = -40°C to +85°C
V _{GATE(hi)}	GATE high output voltage	V _{DD} -0.3		V _{DD}	V	I _{OUT} = 10mA
V _{GATE(lo)}	GATE low output voltage	0		0.3	V	I _{OUT} = -10mA
f _{osc}	Oscillator frequency	20 80	25 100	30 120	kHz	R _{OSC} = 1.00MOhm R _{OSC} = 226kOhm
D_{MAXhf}	Maximum oscillator PWM duty cycle			100%		F _{PWM hf} = 25kHz, at GATE, CS to GND
V _{LD}	Pin LD (linear dimming) voltage range	0		250	mV	T _A = <85°C, V _{IN} = 12V
T _{BLANK}	Current sense blanking interval	150	215	280	ns	$V_{CS} = 0.55 V_{LD}, V_{LD} = V_{DD}$
t DELAY	Delay from CS to GATE lo			300	ns	V_{IN} = 12V, V_{LD} = 0.15, V_{CS} = 0 to 0.22V after T _{BLANK}
t _{RISE}	GATE output rise time	30		50	ns	$C_{GATE} = 500 \text{pF}, V_{DD} = 7.5 \text{V}$
t _{FALL}	GATE output fall time	30		50	ns	$C_{GATE} = 500 pF, V_{DD} = 7.5 V$

Note:

1. Also limited by package power dissipation limit, whichever is lower.



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BLOCK DIAGRAM



Application Note

Oscillator

The oscillator in the HM9910 is controlled by a single resistor connected at the RT pin. The equation governing the oscillator time period $t_{\rm osc}$ is given by:

$$t_{\rm OSC}(\mu s) = \frac{R_{\rm T}(k\Omega) + 22}{25}$$

If the resistor is connected between RT and GND, HM9910 operates in a constant frequency mode and the above equation determines the time-period. If the resistor is connected between RT and GATE, the HM9910 operates in a constant off-time mode and the above equation determines the offtime.

Current Sense Resistor

The formula for calculation of Iled for HM9910 in typical application circuit is:

$$R_{cs} = \frac{0.25V \text{ (or } V_{LD})}{1.15 \cdot I_{LED} \text{ (A)}}$$



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SOP8 PACKAGE OUTLINE DIMENSIONS



Cumb a l	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Max	
A	1.350	1. 750	0. 053	0.069	
A1	A1 0. 100		0.004	0.010	
A2	1.350	1. 550	0. 053	0. 061	
b	0. 330	0. 510	0.013	0. 020	
С	0. 170	0. 250	0.006	0.010	
D	4. 700	5. 100	0. 185	0. 200	
E	3.800	4.000	0. 150	0. 157	
E1	5.800	6. 200	0. 228	0. 244	
е	1. 270 (BSC)		0. 050 (BSC)		
L	0. 400	1. 270	0.016	0.050	
θ	0°	8°	0°	8°	